Silicon PNP Power Transistors 2SB1495

DESCRIPTION

·With TO-220F package
·Complement to type 2SD2257
·High DC current gain.
·Low saturation voltage.
·DARLINGTON

APPLICATIONS

·High power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

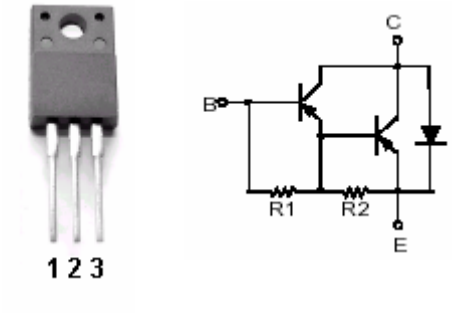


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-8	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-5	A
I_B	Base current		-0.3	A
P_C	Collector dissipation	T_C=25□	20	W
		T_a=25□	2	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA; I_B=0	-100			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1.5A ; I_B=-1.5mA			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-1.5A ; I_B=-1.5mA			-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-100V;I_E=0			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-8V;I_C=0			-4.0	mA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-2V	2000			
h_{FE-2}	DC current gain	I_C=-2A ; V_{CE}=-2V	2000			

Switching times

t_{on}	Turn-on time	I_{B1}=-I_{B2}=-1.5mA V_{CC}≈-30V ,R_L=20Ω		0.5		μs
t_s	Storage time			1.0		μs
t_f	Fall time			0.4		μs

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PACKAGE OUTLINE

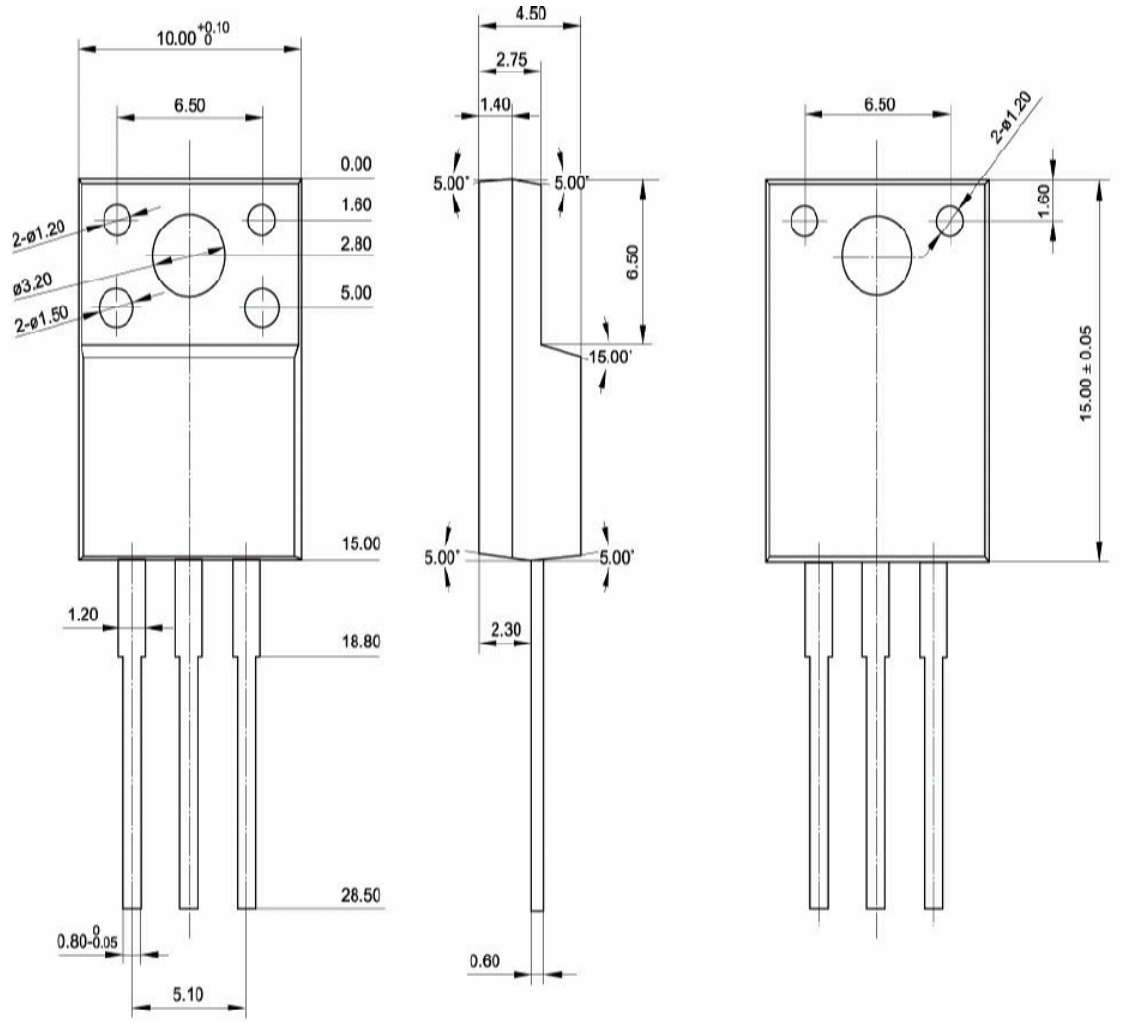


Fig.2 Outline dimensions